Silicon NPN Power Transistors 2SD748 2SD748A

DESCRIPTION

·With TO-3 package
·High V_{CBO}
·High power dissipation

APPLICATIONS

·Low frequency power amplifier regulator
for TV power supply applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage		Open emitter	250	V
V_{CEO}	Collector-emitter voltage	2SD748	Open base	200	V
		2SD748A		250	
V_{EBO}	Emitter-base voltage		Open collector	5	V
I_C	Collector current			3	A
I_B	Base current			1	A
P_C	Collector power dissipation		T_C=25□	80	W
T_j	Junction temperature			150	□
T_{stg}	Storage temperature			-45~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SD748	I_C=10mA ;R_{BE}=∞	200			V
		2SD748A		250			
$V_{(BR)EBO}$	Emitter-base breakdown voltage		I_E=5mA ;I_C=0	5			V
V_{CEsat}	Collector-emitter saturation voltage		I_C=3A; I_B=0.6A			1.0	V
V_{BE}	Base-emitter on voltage		I_C=1A ; V_{CE}=5V			1.5	V
I_{CBO}	Collector cut-off current		V_{CB}=200V; I_E=0			1.0	mA
I_{EBO}	Emitter cut-off current		V_{EB}=5V; I_C=0			1.0	mA
h_{FE}	DC current gain		I_C=1A ; V_{CE}=5V	25		200	

PACKAGE OUTLINE

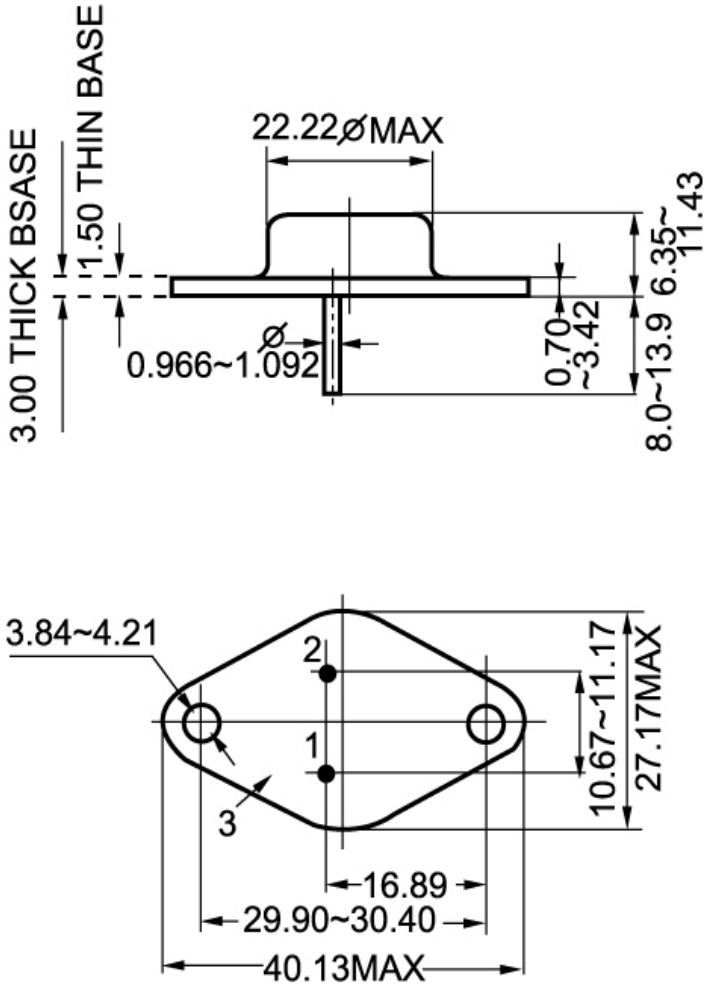

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)